

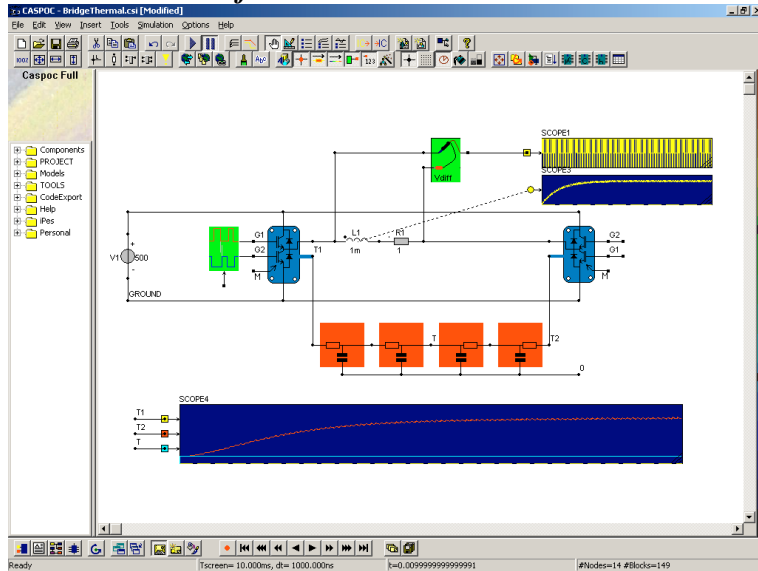
Caspoc

Fast and Easy Power Electronics and Electrical Drives Simulation

Semiconductors Detailed and Fast

Optimize your power electronic designs by using the "fast power loss prediction models" in Caspoc.

Fast simulation of the losses in an IGBT inverter



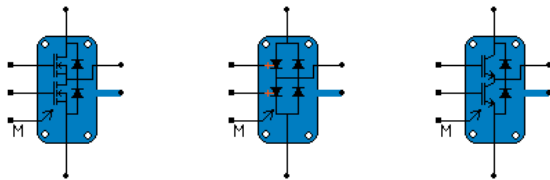
Features:

- Detailed mosfet models with non-linear capacitance's
- IGBT models with tail current
- Diode models with reverse recovery
- Fast loss-prediction models for fast simulation
- Coupling to Thermal models
- Include parasitic wire inductance and bus-bar capacitance in the circuit

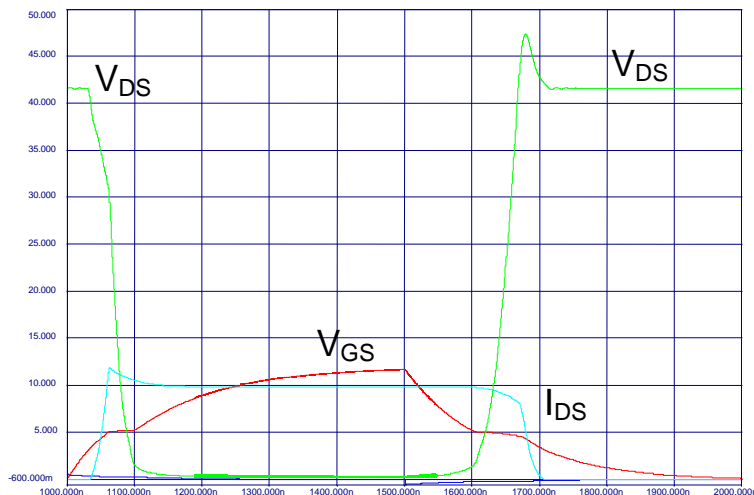
Diode Reverse Recovery

The reverse recovery in a diode is dependent on the maximum forward current and its slope during turn off. Increasing the inductance in each successive simulation increases the slope of the turn-off current and thereby decreasing the reverse recovery current.

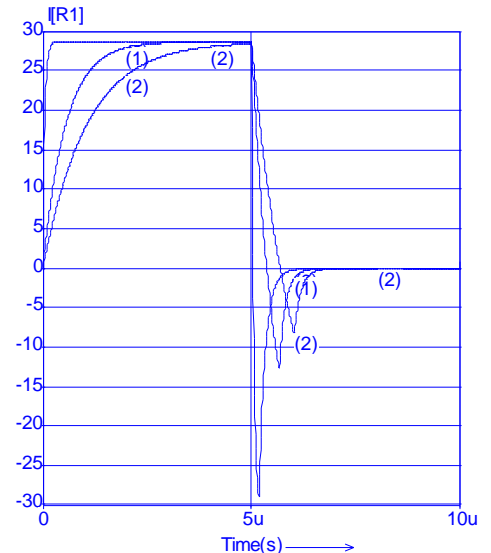
Fast Loss Predicting Semiconductor Models



Detailed Mosfet Modeling



Detailed modeling of a mosfet in Caspoc reveals the on and off switching waveforms.



Summarizing,
use detailed semiconductor models or
loss-prediction models
quick and easy.